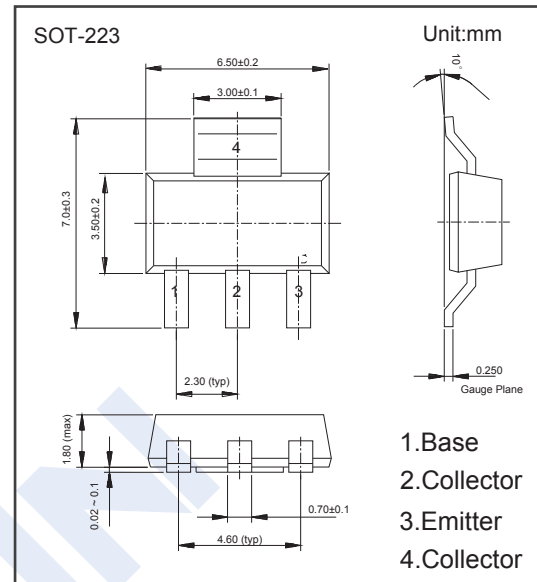


NPN Transistors 2KD3009

■ Features

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complements to 2KB4017



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	100	V
Collector - Emitter Voltage	V _{CEO}	80	
Emitter - Base Voltage	V _{EBO}	5	
Collector Current - Continuous	I _C	1	A
Collector Power Dissipation	P _C	1.5	W
Thermal Resistance Junction to Ambient	R _{θJA}	83.3	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

NPN Transistors 2KD3009

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E = 0	100			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 10 mA, I _B = 0	80			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _C = 0	5			
Collector-base cut-off current	I _{CB0}	V _{CB} = 100 V, I _E = 0			0.1	uA
Emitter cut-off current	I _{EB0}	V _{EB} = 5V, I _C =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500 mA, I _B =50mA			0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =500 mA, I _B =50mA			1.2	
Base-emitter voltage	V _{BE}	V _{CE} = 2V, I _C = 500mA			1	
DC current gain	h _{FE(1)}	V _{CE} = 2V, I _C = 5mA	25			
	h _{FE(2)}	V _{CE} = 2V, I _C = 150mA	100		250	
	h _{FE(3)}	V _{CE} = 2V, I _C = 500mA	25			
Transition frequency	f _T	V _{CE} = 10V, I _C = 50mA, f=100MHz	100			MHz

■ Marking

Marking	KN56 K****
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NPN Transistors 2KD3009

■ Typical Characteristics

